

FIG. 1A

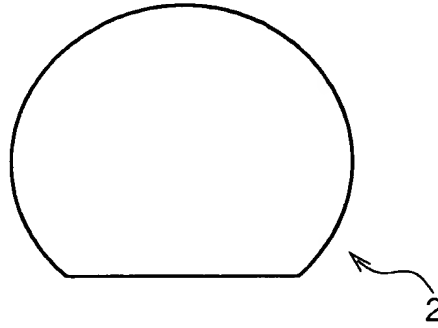


FIG. 1B

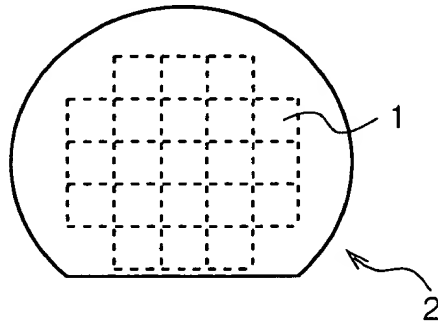


FIG. 1C

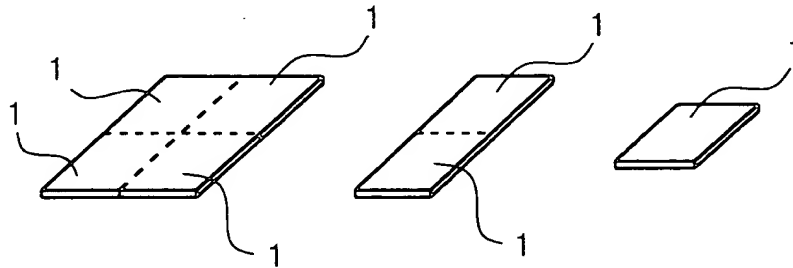


FIG. 1D

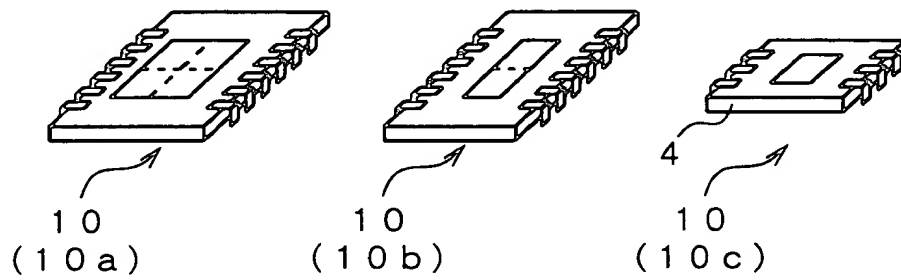
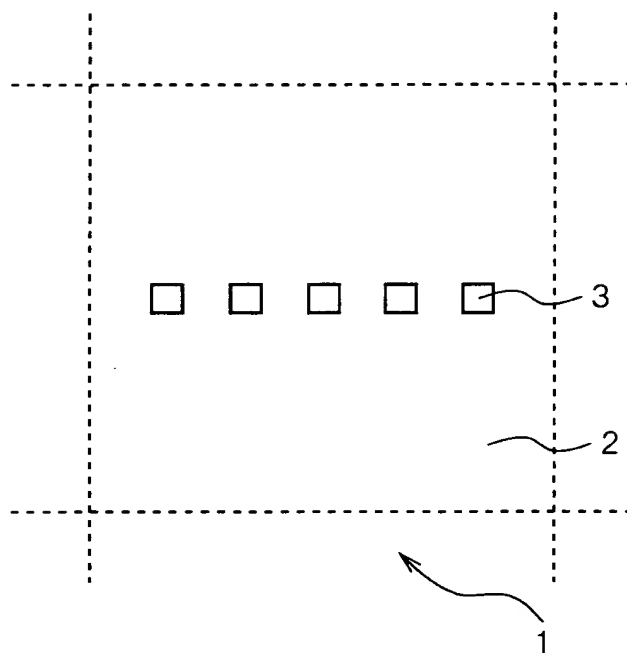


FIG. 2



004544-111200

3/5

FIG. 3A

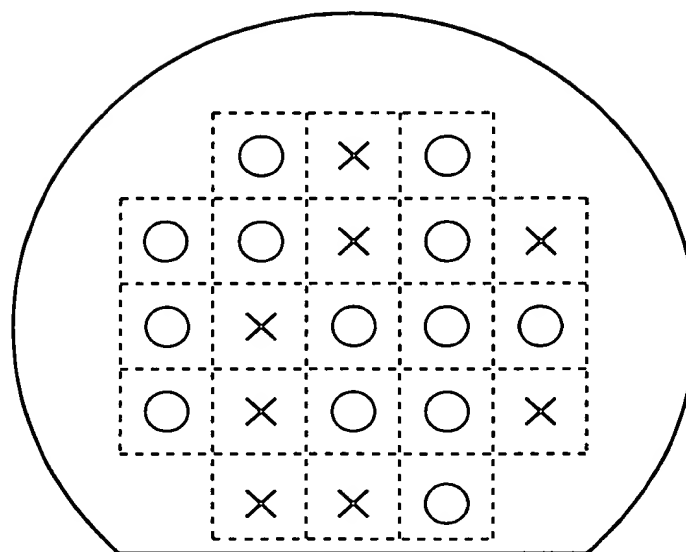
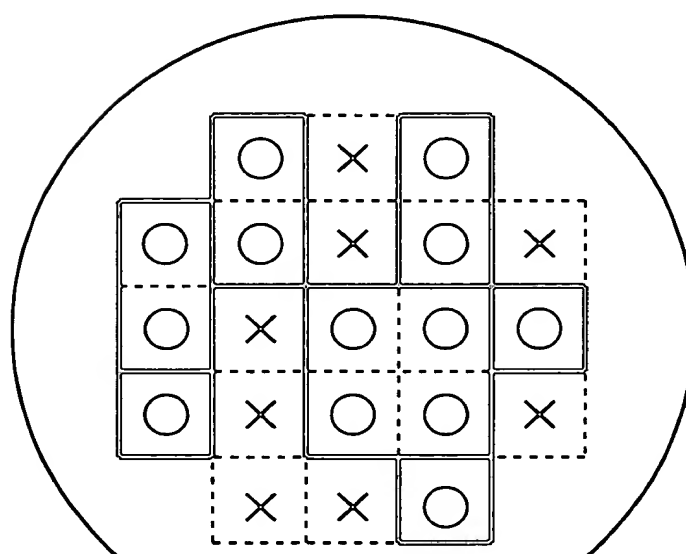


FIG. 3B



00245043-111700

FIG. 4A

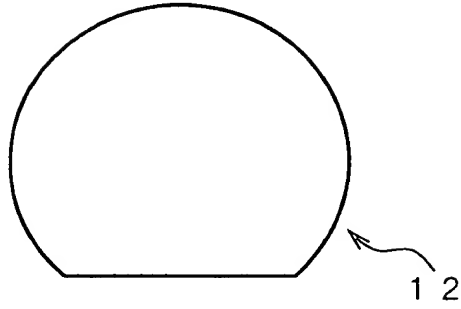


FIG. 4B

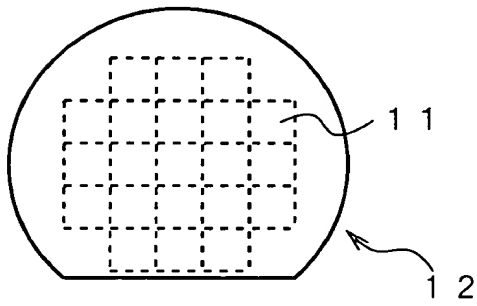


FIG. 4C

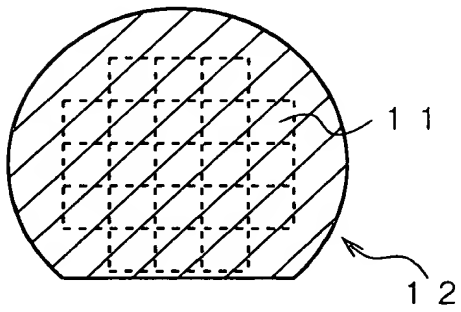
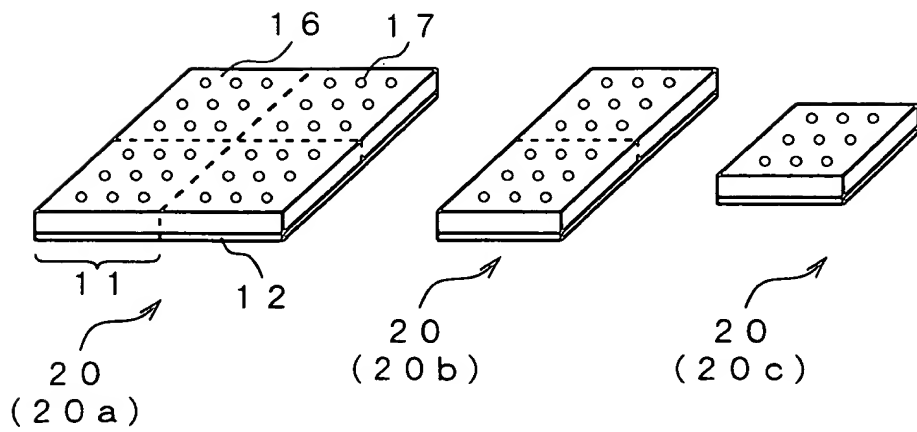


FIG. 4D



A cross-sectional view of a semiconductor device 100. The device consists of a substrate 102 with a thin layer 103 on its top surface. A series of rectangular pillars 104 are formed on layer 103, each topped with a spherical cap 107. The pillars are separated by grooves 105. A layer 106 is formed on the top surface of the pillars and in the grooves. An arrow 101 points to the entire structure.